

POWER MOS FETs (2)

The Sanyo J-MOS series utilizes Sanyo's own fine fabrication process for power devices to develop an entire series of ultrahigh performance power devices capable of high voltage, high speed and large current operation.

With performance of wide applications for virtually any types of power electronic equipment, the UH Series, AP Series and LD Series offer the most suitable devices to meet specific needs.

In addition to the above we have Small-signal MOS FETs. See other pages.

AP Series (Advanced Performance)

VDSS 100V system (*:PD value at Tc=25°C)

※RDS(on):VGS=10V

Type No.	Package	Absolute Maximum Ratings /Ta=25℃					Electrical Characteristics/Ta=25℃			Type No.
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	I _{DP} (A)	* P _D (W)	V _{GS(off)} (V)	※ R _{DS(on)} typ/max (Ω)	C _{iss} typ (PF)	
2SK1427	TO-220	100	± 20	10	40	40	1.5~2.5	0.12/0.16	750	2SK1427
2SK1428				20	80	60		75m/100m	1200	2SK1428
2SK1429				30	120	70		40m/55m	2400	2SK1429
2SK1430	TO-220ML			10	40	25		0.12/0.16	750	2SK1430
2SK1431				15	60	30		75m/100m	1200	2SK1431
2SK1432				25	100	40		40m/55m	2400	2SK1432
2SK1433	TO-3PB			30	120	100		40m/55m	2400	2SK1433
2SK1434				60	240	150		23m/35m	4800	2SK1434
2SK1435	TO-3PML			30	120	60		40m/55m	2400	2SK1435
2SK1436				50	200	80		23m/35m	4800	2SK1436
2SK1437	TO-3PBL			70	280	200		16m/26m	7200	2SK1437

VDSS 200V, 250V system

(2SJ type:P channel (-) sign is omitted.)

2SK2160	TO-220ML	200	± 20	7	28	25	1.5~2.5	0.35/0.45	550	2SK2160
2SK2161				9	36	25		0.25/0.35	700	2SK2161
2SK2378				13	52	30		0.16/0.21	1100	2SK2378
2SK2379				20	80	40		70 _m /95 _m	2400	2SK2379
2SJ282	TO-220	250	± 30	3	12	50	1.5~2.5	1.5/2	600	2SJ282
2SK1921				4	16	50		0.5/0.7	600	2SK1921
2SK2142				12	48	70		0.25/0.35	1250	2SK2142
2SJ306				3	12	25		1.5/2	600	2SJ306
2SJ307	6			24	30	0.75/1		1250	2SJ307	
2SJ308	9			36	40	0.35/0.48		2700	2SJ308	
2SJ320	4			16	25	1/1.3		750	2SJ320	
2SK2010	4			16	25	0.5/0.7		600	2SK2010	
2SK2011	12			48	30	0.25/0.35		1250	2SK2011	
2SK2012	18			72	40	0.12/0.16		2700	2SK2012	
2SK2108	6			24	25	0.38/0.5		750	2SK2108	
2SK2321	S M P			12	48	70		0.25/0.35	1250	2SK2321
2SK2058	TO-3PB			25	100	120		0.12/0.16	2700	2SK2058

VDSS 450V system

2SK1438	TO-220	450	± 30	0.3	1.2	20	2~3	9/12	90	2SK1438
2SK1439				3	12	50		2/2.6	400	2SK1439
2SK1440				5	20	60		1/1.4	700	2SK1440
2SK1441				8	32	70		0.6/0.8	1200	2SK1441
2SK1442				12	48	70		0.47/0.6	1600	2SK1442
2SK1443LS	TO-220FI (LS)			1	4	20		3.5/4.5	250	2SK1443LS
2SK1444LS				3	12	25		2.0/2.6	400	2SK1444LS
2SK1445LS				5	20	30		1/1.4	700	2SK1445LS
2SK1446LS				7	28	35		0.6/0.8	1200	2SK1446LS
2SK1447LS				9	36	40		0.47/0.6	1600	2SK1447LS
2SK1690	S M P			3	12	50		2/2.6	400	2SK1690
2SK1691				5	20	60		1/1.4	700	2SK1691
2SK1448	TO-3PB			8	32	100		0.6/0.8	1200	2SK1448
2SK1449				12	48	120		0.47/0.6	1600	2SK1449
2SK1450				20	80	150		0.24/0.3	3200	2SK1450
2SK1451	TO-3PML			8	32	50		0.6/0.8	1200	2SK1451
2SK1452				10	40	60		0.47/0.6	1600	2SK1452
2SK1453				16	64	70		0.24/0.3	3200	2SK1453
2SK1454	TO-3PBL			30	120	250		0.12/0.16	6400	2SK1454

VDSS 600V system

2SK1922	TO-220	600	±30	2	8	50	2	~	3	3.2/4.3	400	2SK1922		
2SK1923				4	16	60				1.8/2.4	700	2SK1923		
2SK1924				6	24	70				1.1/1.5	1100	2SK1924		
2SK2043LS	TO-220FI (LS)			2	8	25				3.2/4.3	400	2SK2043		
2SK2044LS				4	16	30				1.8/2.4	700	2SK2044		
2SK2045LS				5.5	22	35				1.1/1.5	1100	2SK2045		
2SK1925	TO-3PB			8	32	120				0.9/1.2	1500	2SK1925		

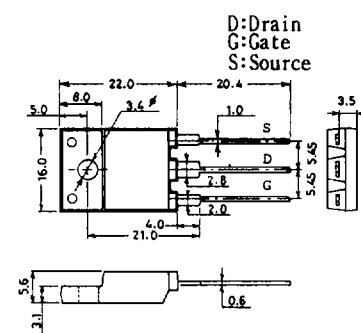
Precaution

◎ Take care to prevent device breakage from static electricity because MOSFETs cannot withstand much static electricity.

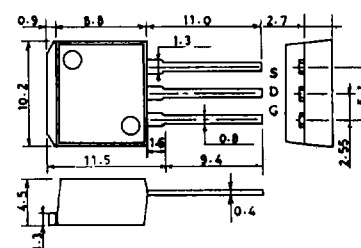
◎ For samples and shipment contact our Product Planning Dept. of TR division.

These specifications are subject to change without notice.

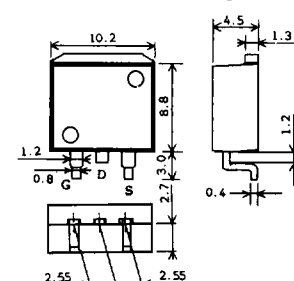
Case Outlines (unit:mm)
SANYO:TO-3PML



SANYO:SMP(straight type)



SANYO:SMP(FD forming)



SANYO:TO-3PBL

